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				Application Number	10719,279 T80
				Filing Date	Herewith 11/21/03
				First Named Inventor	Yuanning Chen, et al.
				Group Art Unit	2813
				Examiner Name	Jack S J Chen
Sheet	1	of	1	Attorney Docket No.	TI-35022.2

U.S. PATENT DOCUMENTS						
Exam. Initials*	Cite No. <sup>1</sup>	U.S. Patent Document		Name of Patentee or Applicant of Cited Doc.	Date of Pub. of Cited Doc. (mm-dd-yyyy)	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
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FOREIGN PATENT DOCUMENTS								
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OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS			
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	CA	RYUTA TSUCHIYA ET AL., "Femto-Second CMOS Technology with High-k Offset Spacer and SiN Gate Dielectric with Oxygen-Enriched Interface" IEEE 2002 Symposium on VLSI Technology Digest of Technical Papers	
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Examiner Signature		Date Considered	5/14/04
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